Semiconductor Fundamentals

Presented to EE2187 class in Semester 1 2019/20

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Lecture 9

Course information

- Semiconductors Materials Types of Solids, Space lattice, Atomic Bonding,
- ❖ Introduction to quantum theory, Schrodinger wave equation, Electron in free space, Infinite well, and step potentials, Allowed and forbidden bands
- Electrical conduction in solids, Density of states functions, Fermi-Dirac distribution in Equilibrium,
- ❖ Valence band and Energy band models of intrinsic and extrinsic Semiconductors. Degenerate and non degenerate doping
- Thermal equilibrium carrier concentration, charge neutrality
- Carrier transport Mobility, drift, diffusion, Continuity equation.

Reference

Text Book:

- 1. Physics of Semiconductor Devices, S. M. Sze, John Wiley & Sons (1981).
- 2. Solid State Electronics by *Ben G. Streetman and Sanjay Banerjee*, Prentice Hall International, Inc.
- 3. Semiconductor Physics and Devices, Donald A. Neamen, Tata Mcgraw-Hill Publishing company Limited.
- 4. Advanced Semiconductor Fundamentals by Pirret

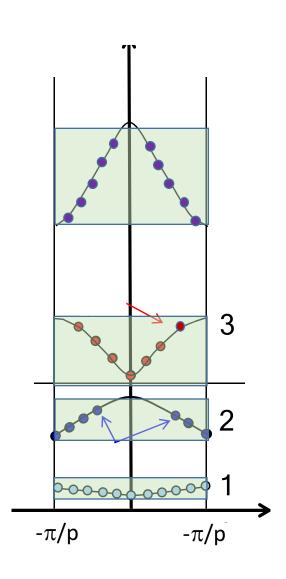
Reference Book:

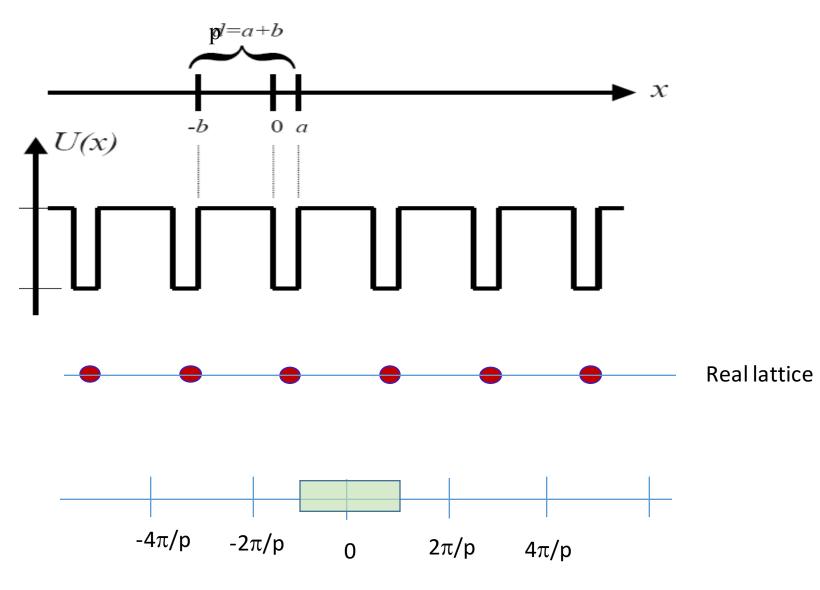
- 1. Fundamentals of Solid-State Electronic Devices, *C. T. Sah*, Allied Publisher and World Scientific, 1991.
- 2. Complete Guide to Semiconductor Devices, K. K. Ng, McGraw Hill, 1995.
- 3. Solid state physics, Ashcroft & Mermins.
- 4. Introduction to Solid State Electronics, E. F. Y. Waug, North Holland, 1980.

Recap



Brillouin Zone





How to get Reciprocal Space Lattice and BZ?

Reciprocal space lattice from real space vector

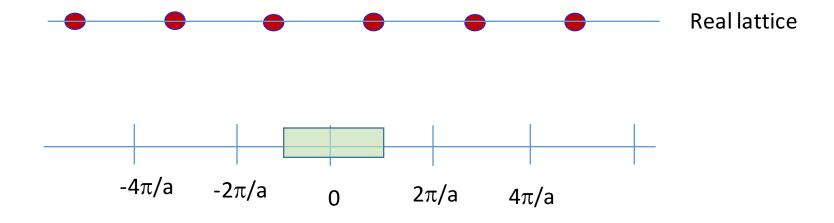
$$K_x = 2\pi \ b \times c/|a.b \times c| = 2\pi \ b \times c/V$$

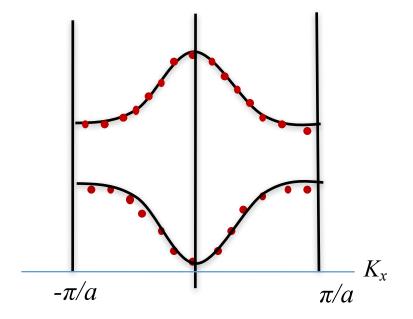
$$K_y = 2\pi \ c \times a/|a.b \times c| = 2\pi \ c \times a/V$$

$$Kz = 2\pi \ a \times b/|a.b \times c| = 2\pi \ a \times b/V$$

For BZ Wigner Size cell in Reciprocal lattice

BZ in 1-D



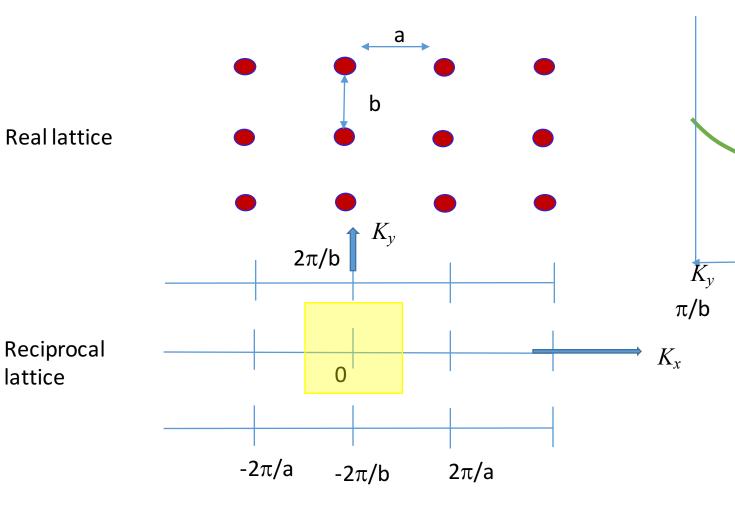


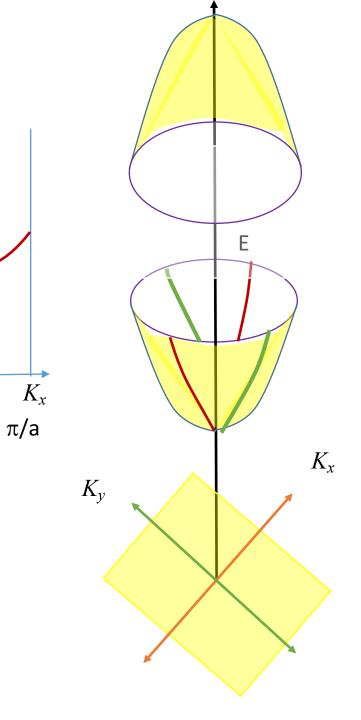
BZ in 2-D

lattice

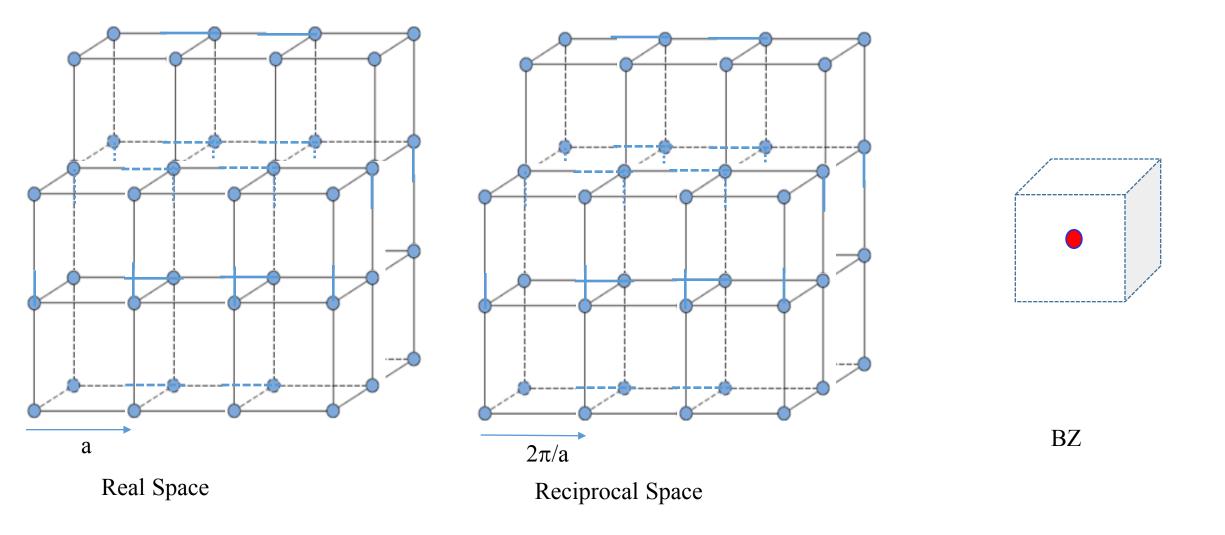
E-K Diagram

Ε



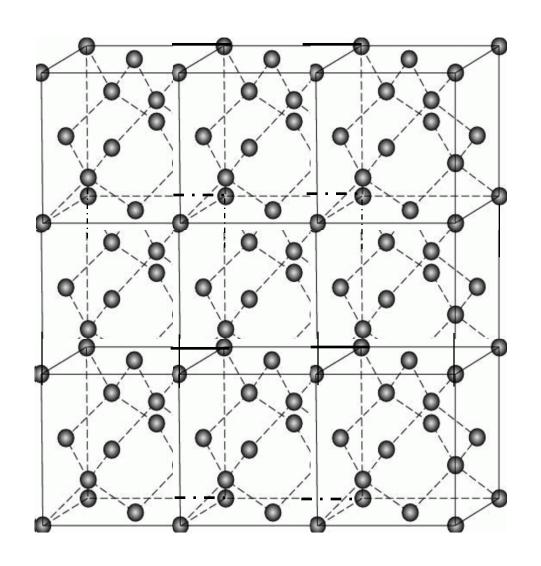


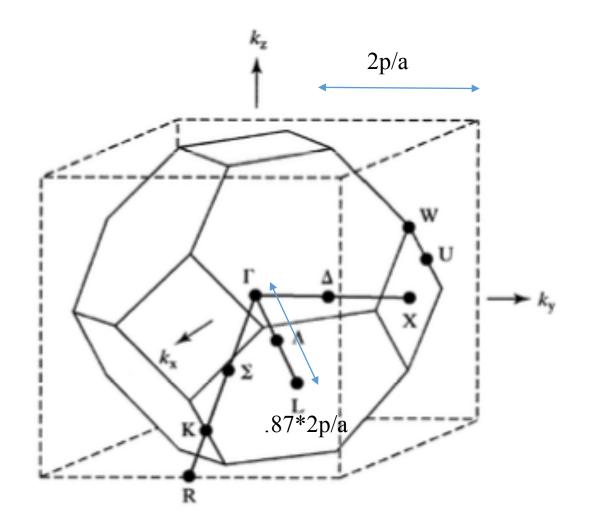
BZ in 3-D



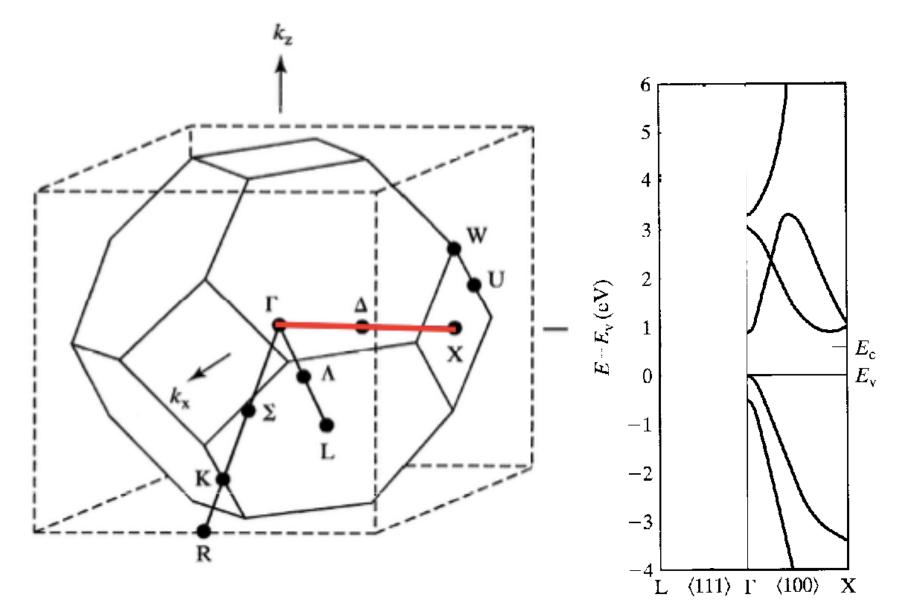
Now; BZ Ge, Si, GaAs

Real Space



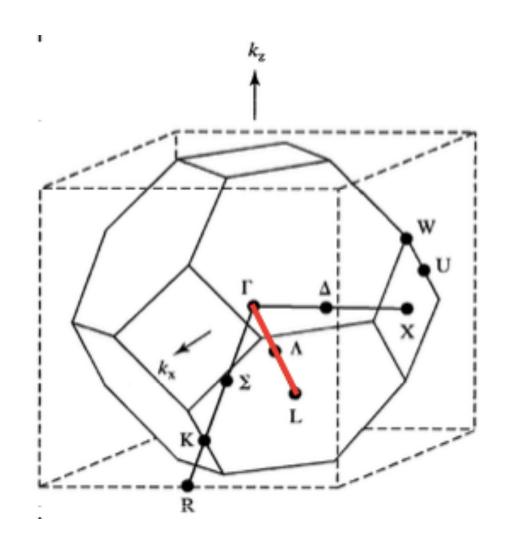


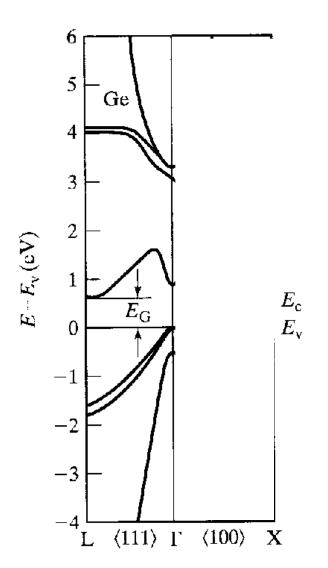
E-K Along X point



- ❖ <100> direction
- $2\pi/a(1,0,0)$ 6 symmetrical point
- (100), (-100),(010), (0-10),(001), (00-1)

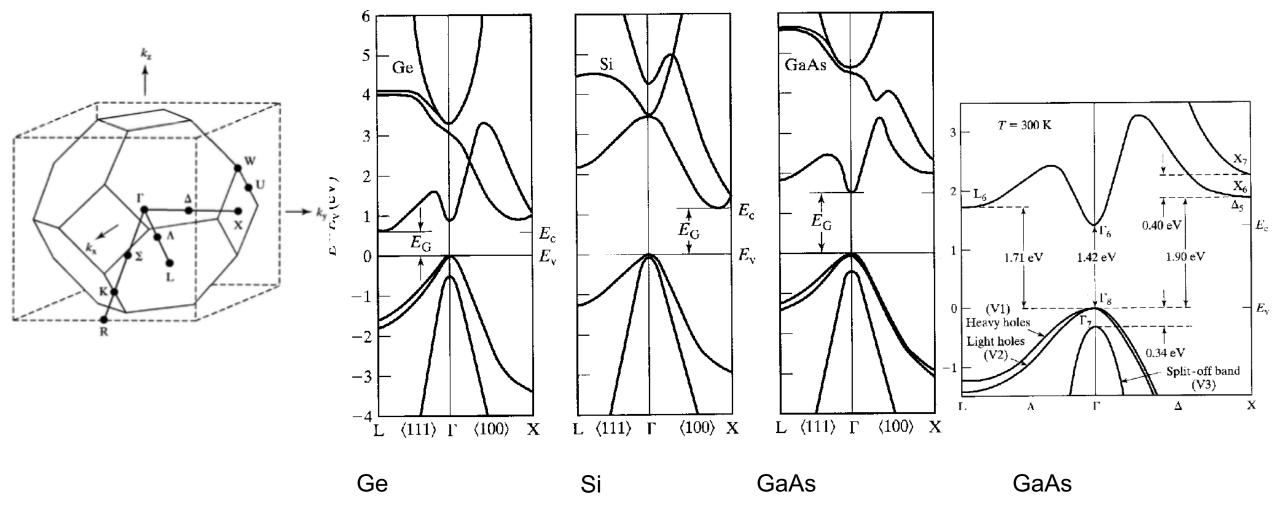
E-K Along L point





- ❖ <111> direction
- $2\pi/a(1/2,1/2,1/2)$ 8 symmetrical point

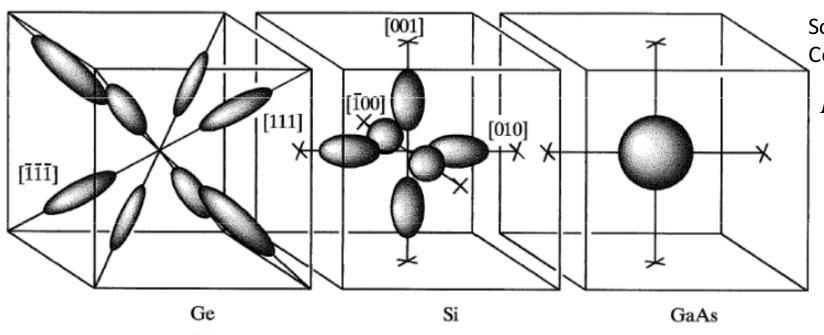
3-D E-k Diagram



X,L points are highly symmetrical, energy stable states

Constant-Energy Surfaces: Conduction Band

Geometrical shapes for given Energy are called CES



For Ge CES occurs at 8 equivalent <111> direction

> For GaAs A=B=C And for Si, and Ge, B=C

For Si CES occurs at 6 equivalent < 100> direction

at Zone center

(c)

So Energy E in Conduction band

$$E = Ec + Ak_1^2 + Bk_2^2 + Ck_3^2$$

k,, k2, k3 are k space coordinate measured from center of band minimum along the principle axis for example Ge it will be center on L point For GaAs CES occurs and one of the axis say k_1 would directed along kx, ky, kz in [111] direction